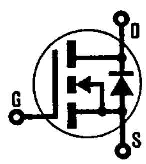
Data Sheet No. PD-9.336D
T-39-11

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

*JANTXV2N6762
*JANTX2N6762
2N6762
2N6761

JEDEC REGISTERED N-CHANNEL POWER MOSFETs



*QUALIFIED TO MIL-S-19500/542

500 Volt, 1.5 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

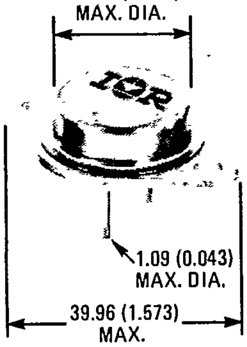
Features:

- Fast Switching
- Low Drive Current
- Ease of Paralleling
- Excellent Temperature Stability

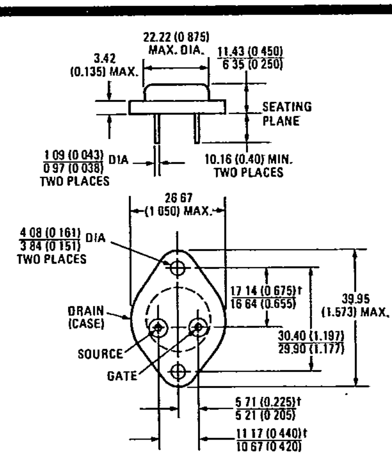
Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
2N6761	450V	2.0Ω	4.0A
2N6762	500V	1.5Ω	4.5A

CASE STYLE AND DIMENSIONS



ACTUAL SIZE



Conforms to JEDEC Outline TO-204AA (TO-3)
Dimensions in Millimeters and (Inches)

JANTXV-, JANTX-, 2N6762 and 2N6761 Devices

Absolute Maximum Ratings

	Parameter	2N6761	2N6762	Units
V_{DS}	Drain – Source Voltage	450*	500*	V
V_{DGR}	Drain – Gate Voltage (R_{GS} = 1 MΩ)	450*	500*	V
I_D @ T_C = 25°C	Continuous Drain Current	4.0*	4.5*	A
I_D @ T_C = 100°C	Continuous Drain Current	2.5*	3.0*	A
I_{DM}	Pulsed Drain Current	6.0	7.0	A
V_{GS}	Gate – Source Voltage	±20*		V
P_D @ T_C = 25°C	Max. Power Dissipation	75* (See Fig. 11)		W
P_D @ T_C = 100°C	Max. Power Dissipation	30* (See Fig. 11)		W
	Linear Derating Factor	0.6* (See Fig. 11)		W/K ②
I_{LM}	Inductive Current, Clamped	(See Fig. 1 and 2) L = 100 μH 6.0	7.0	A
T_J T_{stg}	Operating and Storage Temperature Range	-55* to 150*		°C
	Lead Temperature	300* (0.063 in. (1.6mm) from case for 10s)		°C

Electrical Characteristics @ T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain – Source Breakdown Voltage	2N6761	450	–	–	V	V_{GS} = 0
		2N6762	500	–	–	V	I_D = 4.0 mA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0*	–	4.0*	V	V_{DS} = V_{GS}, I_D = 1 mA
I_{GSSF}	Gate – Body Leakage Forward	ALL	–	–	100*	nA	V_{GS} = 20V
I_{GSSR}	Gate – Body Leakage Reverse	ALL	–	–	100*	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	0.1	1.0*	mA	V_{DS} = 0.8 x Max. Rating, V_{GS} = 0
			–	0.2	4.0*	mA	V_{DS} = Max. Rating, V_{GS} = 0, T_C = 25°C to 125°C
$V_{DS(on)}$	Static Drain-Source On-State Voltage ①	2N6761	–	–	8.0*	V	V_{GS} = 10V, I_D = 4A
		2N6762	–	–	7.7*	V	V_{GS} = 10V, I_D = 4.5A
$R_{DS(on)}$	Static Drain-Source On-State Resistance ①	2N6761	–	1.5	2.0*	Ω	V_{GS} = 10V, I_D = 2.5A
		2N6762	–	1.3	1.5*	Ω	V_{GS} = 10V, I_D = 3.0A
$R_{DS(on)}$	Static Drain-Source On-State Resistance ①	2N6761	–	–	4.4*	Ω	V_{GS} = 10V, I_D = 2.5A, T_C = 125°C
		2N6762	–	–	3.3*	Ω	V_{GS} = 10V, I_D = 3.0A, T_C = 125°C
g_{fs}	Forward Transconductance ①	ALL	2.5*	3.5	7.5*	S (℧)	V_{DS} = 16V, I_D = 3A
C_{iss}	Input Capacitance	ALL	350*	600	800*	pF	V_{GS} = 0, V_{DS} = 25V, f = 1.0 MHz
C_{oss}	Output Capacitance	ALL	25*	100	200*	pF	See Fig. 10
C_{rss}	Reverse Transfer Capacitance	ALL	15*	30	60*	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	–	30*	ns	V_{DD} ≅ 225V, I_D = 3A, Z_o = 15Ω
t_r	Rise Time	ALL	–	–	30*	ns	(See Figs. 13 and 14)
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	–	55*	ns	(MOSFET switching times are essentially
t_f	Fall Time	ALL	–	–	30*	ns	independent of operating temperature.)

Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.67*	K/W ②	
R_{thCS}	Case-to-Sink	ALL	–	0.1	–	K/W ②	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	30	K/W ②	Typical socket mount

Body-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	2N6761	–	–	4.0*	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		2N6762	–	–	4.5*		
I_{SM}	Pulsed Source Current (Body Diode)	2N6761	–	–	6.0	A	
		2N6762	–	–	7.0		
V_{SD}	Diode Forward Voltage ①	2N6761	0.65*	–	1.3*	V	T_C = 25°C, I_S = 4A, V_{GS} = 0
		2N6762	0.7*	–	1.4*	V	T_C = 25°C, I_S = 4.5A, V_{GS} = 0
t_{rr}	Reverse Recovery Time	ALL	–	500	–	ns	T_J = 150°C, I_F = I_{SM}, dI_F/dt = 100 A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	7.0	–	μC	T_J = 150°C, I_F = I_{SM}, dI_F/dt = 100 A/μs

*JEDEC registered values. ① Pulse Test: Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2% ② K/W = °C/W, W/K = W/°C

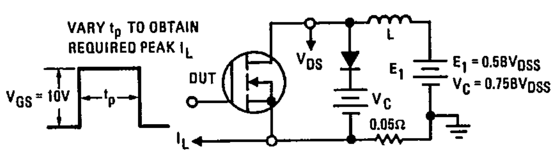


Fig. 1 – Clamped Inductive Test Circuit

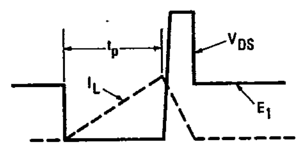


Fig. 2 – Clamped Inductive Waveforms

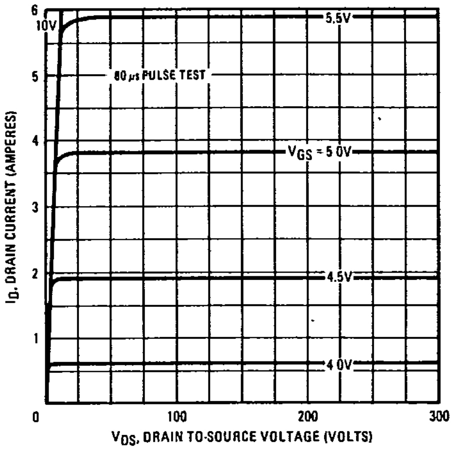


Fig. 3 – Typical Output Characteristics

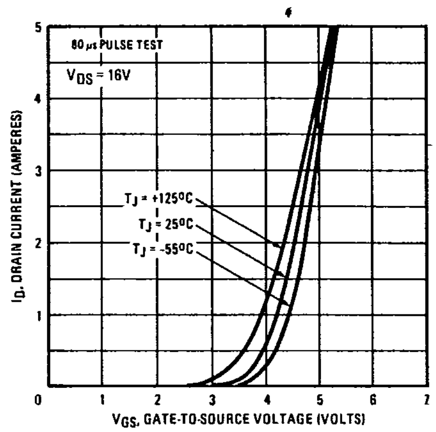


Fig. 4 – Typical Transfer Characteristics

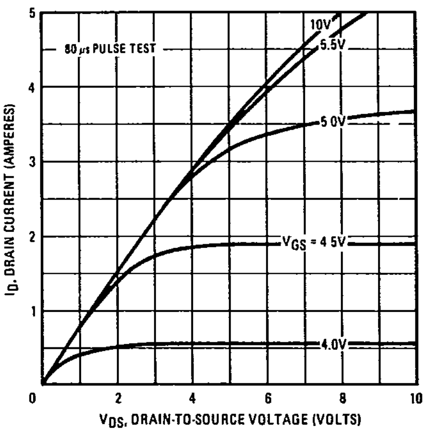


Fig. 5– Typical Saturation Characteristics (2N6761)

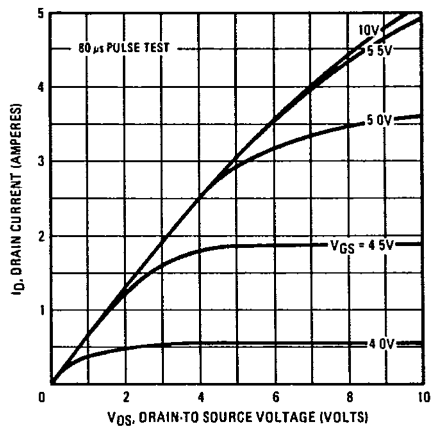


Fig. 6– Typical Saturation Characteristics (2N6762)

TO-3

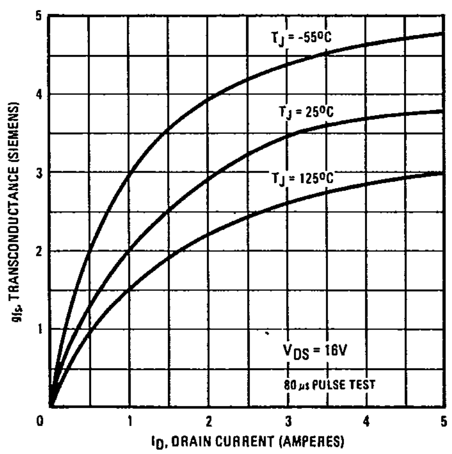


Fig. 7 – Typical Transconductance Vs. Drain Current

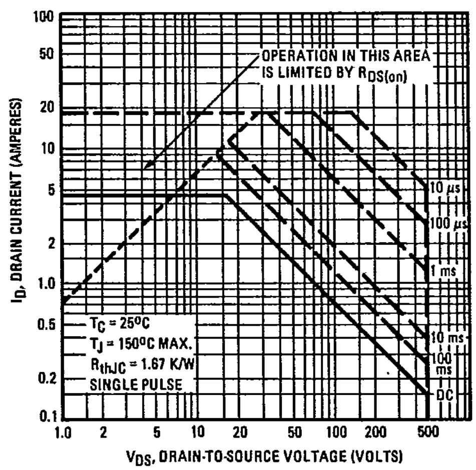


Fig. 8 – Maximum Safe Operating Area

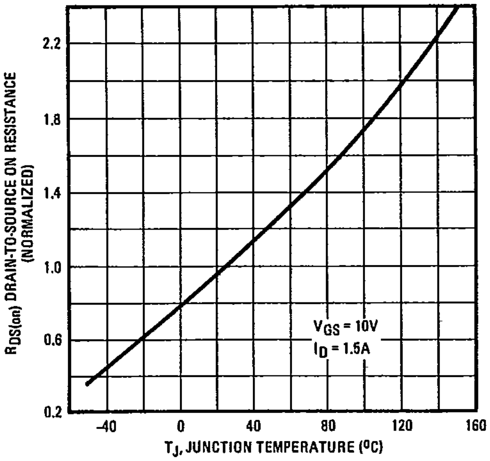


Fig. 9 — Normalized Typical On-Resistance Vs. Temperature

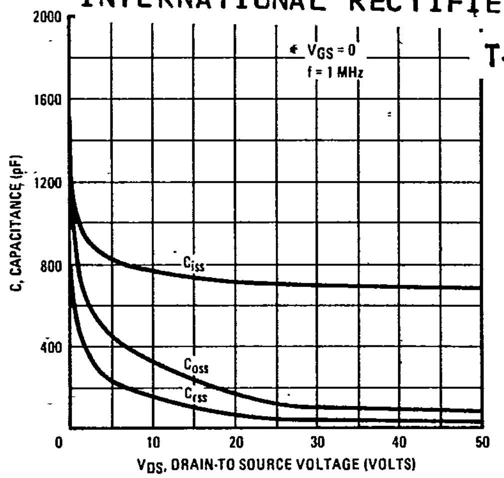


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

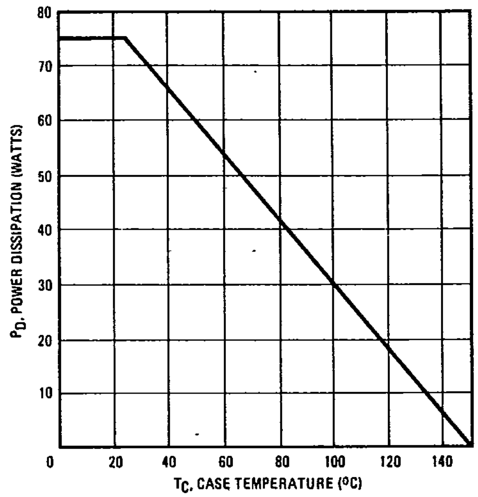


Fig. 11 — Power Vs. Temperature Derating Curve

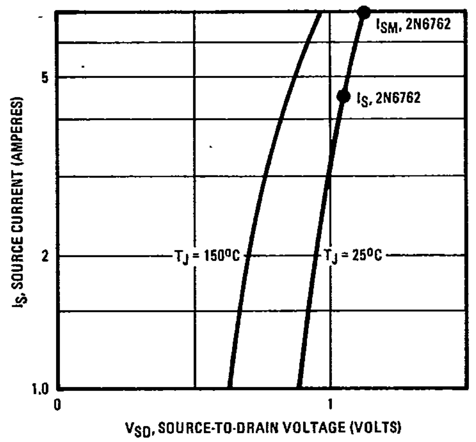


Fig. 12 — Typical Body-Drain Diode Forward Voltage

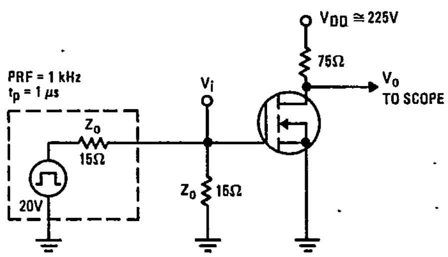


Fig. 13 — Switching Time Test Circuit

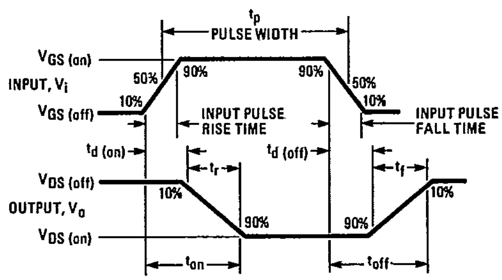


Fig. 14 — Switching Time Waveforms